74AUP3G0434

Low-power dual inverter and single buffer Rev. 2 — 17 January 2013

Product data sheet

General description 1.

The 74AUP3G0434 is a dual inverter and single buffer.

Schmitt trigger action at all inputs makes the circuit tolerant of slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AUP3G0434DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1					
74AUP3G0434GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1					
74AUP3G0434GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089					
74AUP3G0434GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3 \times 2 \times 0.5$ mm	SOT996-2					
74AUP3G0434GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 \times 1.6 \times 0.5 mm	SOT902-2					
74AUP3G0434GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116					
74AUP3G0434GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1.0 \times 0.35 mm	SOT1203					

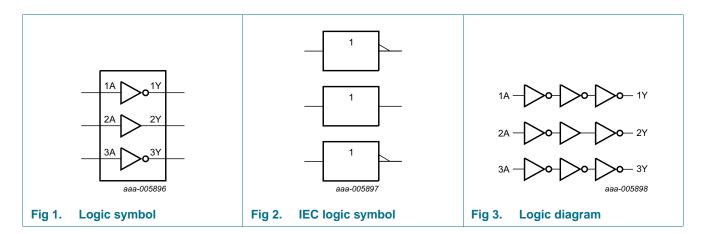
4. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74AUP3G0434DC	pZ
74AUP3G0434GT	pΖ
74AUP3G0434GF	pΖ
74AUP3G0434GD	pΖ
74AUP3G0434GM	pΖ
74AUP3G0434GN	pΖ
74AUP3G0434GS	pZ

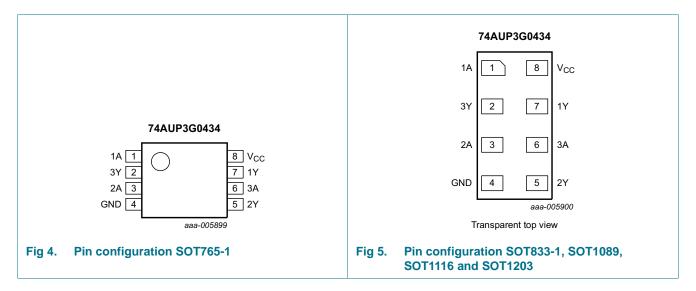
^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

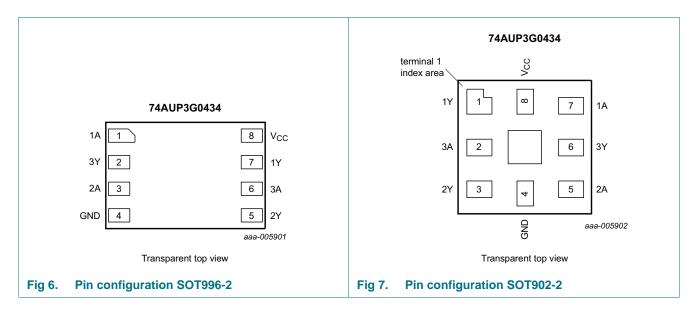
5. Functional diagram



6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description	
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2	
1A, 2A, 3A	1, 3, 6	7, 5, 2	data input
1Y, 2Y, 3Y	7, 5, 2	1, 3, 6	data output
GND	4	4	ground (0 V)
V_{CC}	8	8	supply voltage

7. Functional description

Table 4. Function table[1]

Input 1A,3A	Output
1A,3A	1Y, 3Y
L	Н
Н	L

^[1] H = HIGH voltage level; L = LOW voltage level.

Table 5. Function table [1]

Input	Output
2A	2Y
L	L
Н	Н

^[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	$V_I < 0 V$	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] -	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 7. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		8.0	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	200	ns/V

^[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.
For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$T_{amb} = 2$	25 °C					
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$	$0.70V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	$0.65V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 0.8 \text{ V}$	-	-	$0.30V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.75V _{CC}	-	-	V
		$I_O = -1.7 \text{ mA}$; $V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	0.3V _{CC}	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I _I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μА
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
Δl _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	40	μА
Cı	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$	-	1.0	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.8	-	pF

 Table 8.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C					
V_{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.7V _{CC}	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	0.3V _{CC}	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I _I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μΑ
Δl _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ

 Table 8.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70V _{CC}	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30V _{CC}	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
√он	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V _{CC} - 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.6V _{CC}	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
I	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
OFF	power-off leakage current	V_{I} or $V_{O} = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$	-	-	±0.75	μΑ
∆l _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μΑ
CC	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μΑ
7l ^{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol Parameter		Conditions		25 °C		-40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F				ı				
t _{pd}	propagation delay	nA to nY; see Figure 8							
		$V_{CC} = 0.8 \text{ V}$	-	16.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.4	5.0	10.3	2.0	11.4	12.6	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	1.8	3.6	6.4	1.6	7.4	8.2	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.5	2.9	5.0	1.4	5.9	6.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.2	2.4	3.9	1.1	4.5	5.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.1	2.1	3.2	1.0	3.9	4.3	ns
C _L = 10	ρF								
t _{pd}	propagation delay	nA to nY; see Figure 8							
		$V_{CC} = 0.8 V$	-	19.8	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.8	5.9	12.2	2.3	13.7	15.1	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.3	4.2	7.5	1.9	8.7	9.6	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.0	3.5	5.9	1.7	7.0	7.7	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7	2.9	4.6	1.5	5.4	6.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.6	2.7	3.8	1.4	4.5	5.1	ns
C _L = 15	ρF								
t_{pd}	propagation delay	nA to nY; see Figure 8							
		$V_{CC} = 0.8 \text{ V}$	-	23.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.2	6.7	13.0	2.6	15.8	17.4	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.6	4.7	8.6	2.2	10.0	11.0	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.3	4.0	6.7	2.0	8.0	8.8	ns
		V_{CC} = 2.3 V to 2.7 V	2.1	3.3	5.1	1.8	6.1	6.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	3.1	4.2	1.6	5.0	5.5	ns
$C_L = 30$	ρF								
t_{pd}	propagation delay	nA to nY; see Figure 8							
		$V_{CC} = 0.8 \text{ V}$	-	33.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	4.4	8.9	16.3	3.6	19.0	20.9	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	3.6	6.3	10.8	3.2	12.9	14.2	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	3.2	5.3	9.0	2.9	10.5	11.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.9	4.5	6.5	2.6	7.6	8.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.9	4.2	5.6	2.5	6.2	7.2	ns

 Table 9.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C			-40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pF$	F, 10 pF, 15 pF and	30 pF								
C_{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[3][4]							
		$V_{CC} = 0.8 \text{ V}$		-	2.5	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V		-	2.7	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	2.8	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	3.0	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	3.5	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	4.0	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] All specified values are the average typical values over all stated loads.
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$$
 where:

f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

C_L = load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

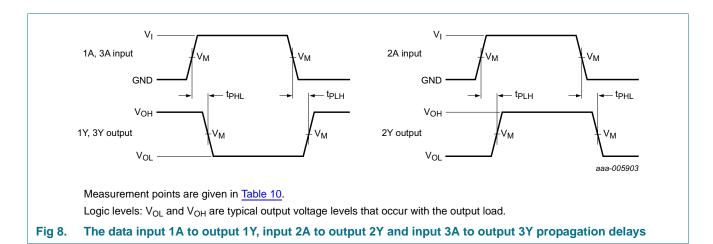
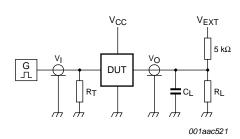


Table 10. Measurement points

Supply voltage	Output	Input				
V _{CC}	V _M	V _M	VI	$t_r = t_f$		
0.8 V to 3.6 V	0.5V _{CC}	0.5V _{CC}	V _{CC}	≤ 3.0 ns		



Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Load		V _{EXT}			
V _{CC}	C _L	R _L [1]	t _{PLH} , t _{PHL}	t_{PZH} , t_{PHZ}	t _{PZL} , t _{PLZ}	
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF, and 30 pF	5 k Ω or 1 M Ω	open	GND	2V _{CC}	

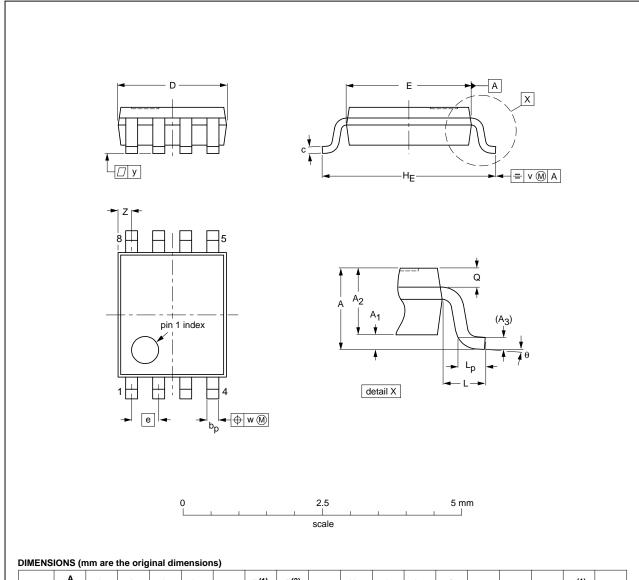
[1] For measuring enable and disable times, R_L = 5 k Ω .

For measuring propagation delays, setup and hold times, and pulse width, R_L = 1 M Ω .

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT765-1		MO-187				02-06-07

Fig 10. Package outline SOT765-1 (VSSOP8)

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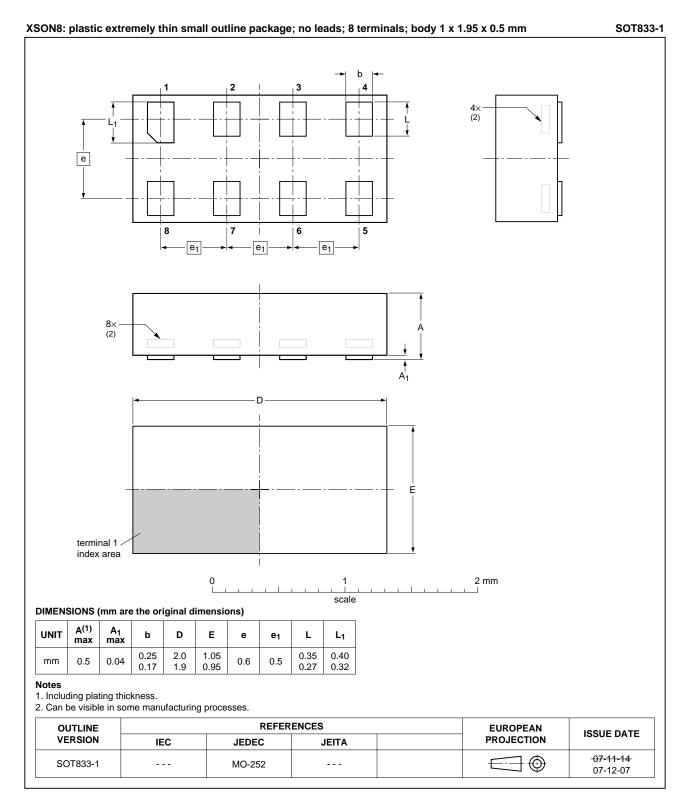


Fig 11. Package outline SOT833-1 (XSON8)

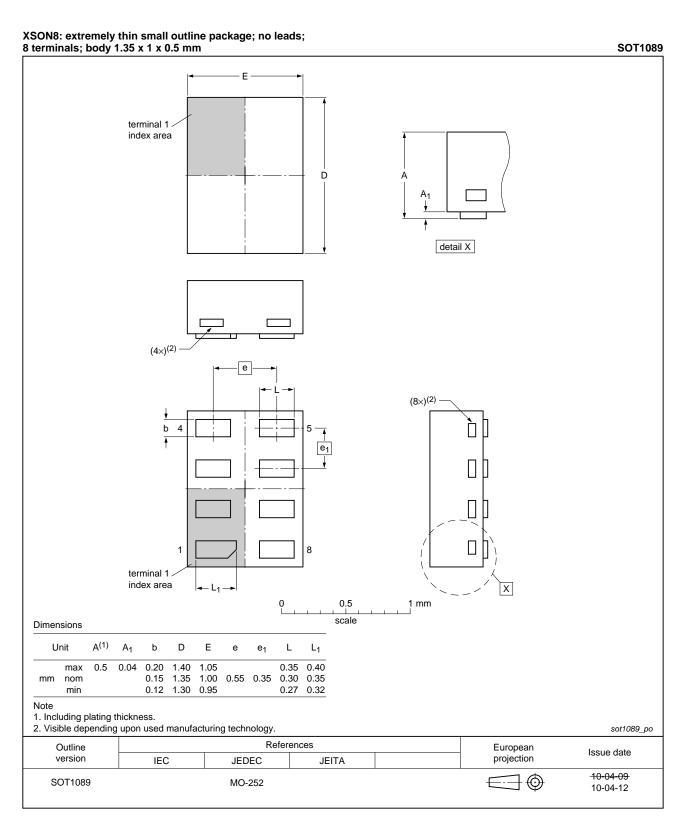


Fig 12. Package outline SOT1089 (XSON8)

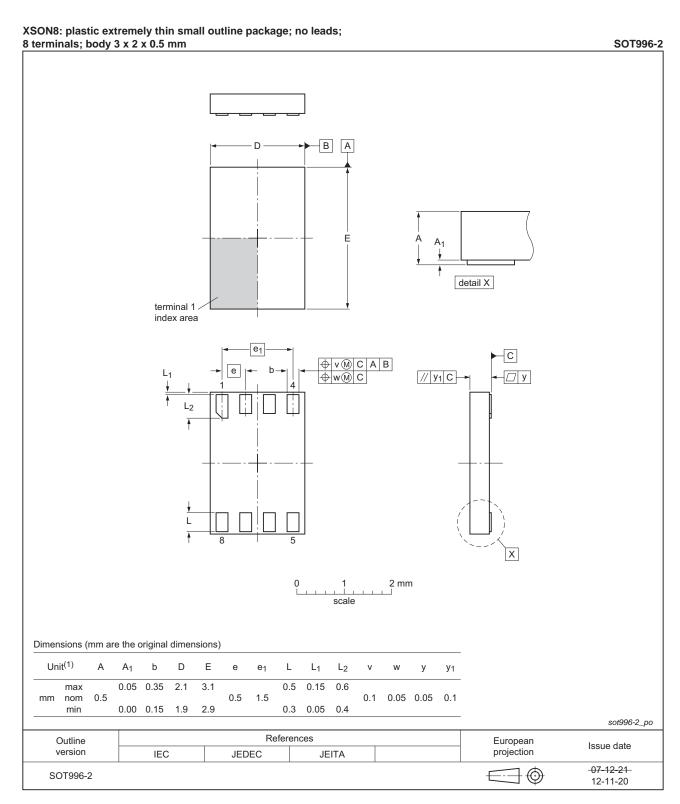


Fig 13. Package outline SOT996-2 (XSON8)

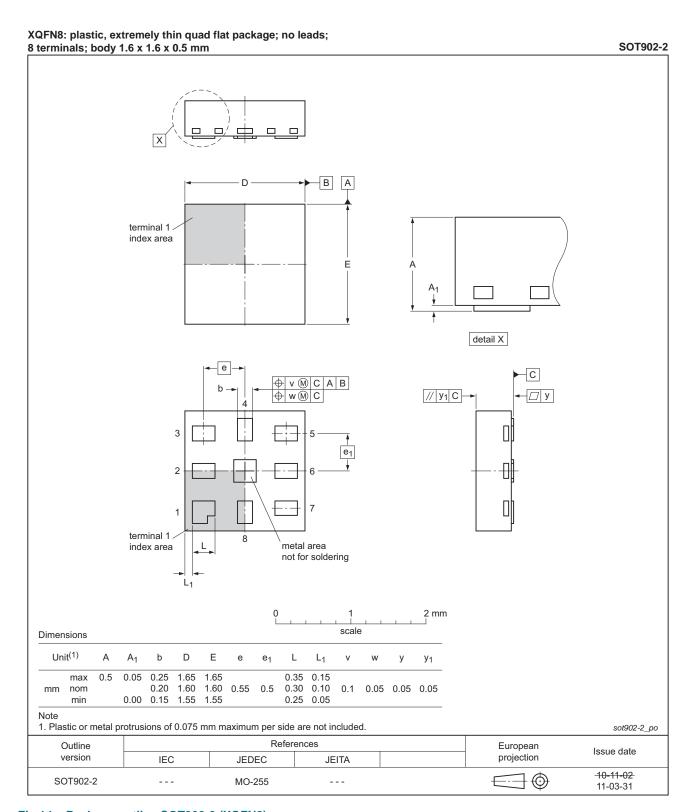


Fig 14. Package outline SOT902-2 (XQFN8)

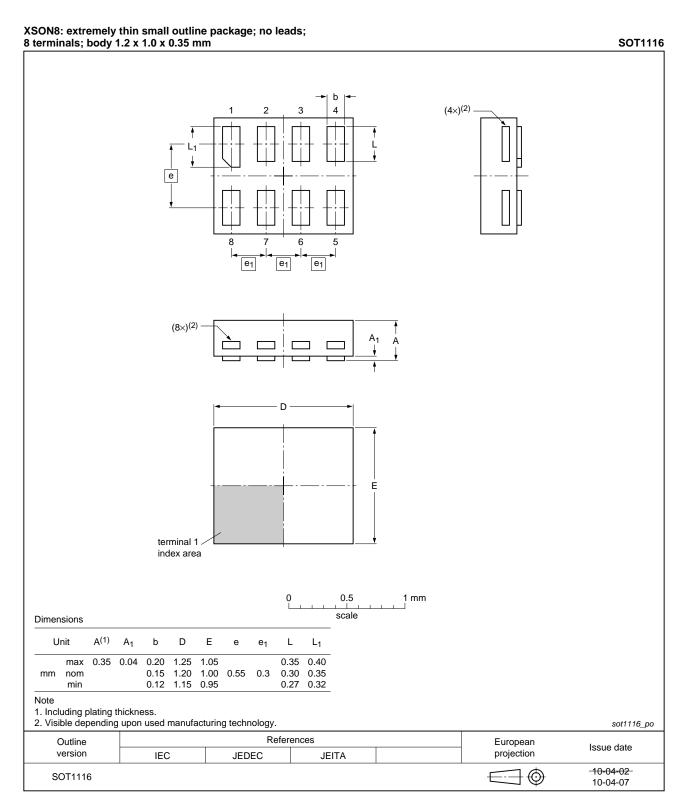


Fig 15. Package outline SOT1116 (XSON8)

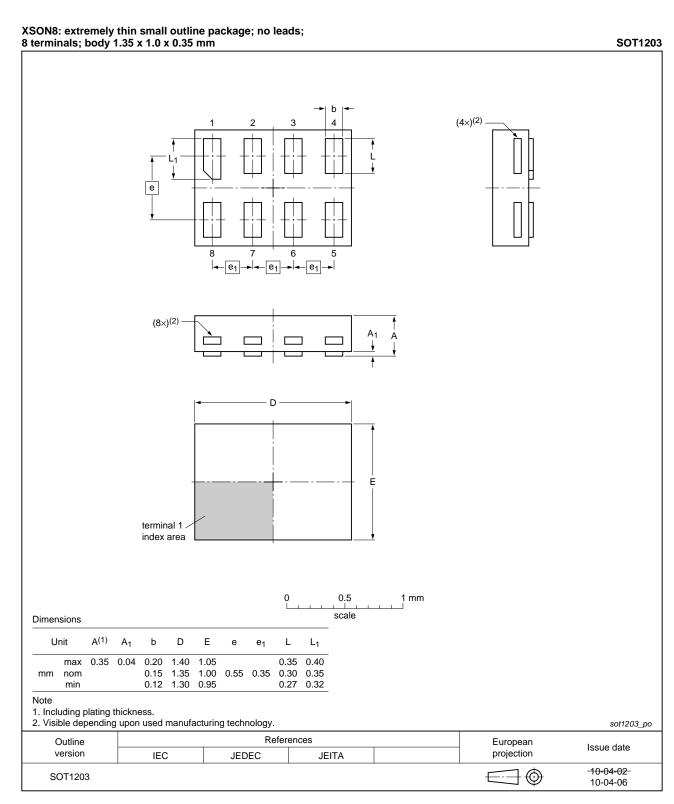


Fig 16. Package outline SOT1203 (XSON8)

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP3G0434 v.2	20130117	Product data sheet	-	74AUP3G0434 v.1
Modifications:	 For type null 	mber 74AUP3G0434GD X	SON8U has changed to	XSON8.
74AUP3G0434 v.1	20121217	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Low-power dual inverter and single buffer

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